This technology is currently not available for licensing

Tech ID: 31869

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- High-Quality N-Face GaN, InN, AlN by MOCVD
- Defect Reduction in GaN films using in-situ SiNx Nanomask
- A Structure For Increasing Mobility In A High-Electron-Mobility Transistor
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- Methods for Locally Changing the Electric Field Distribution in Electron Devices
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors
- Novel Current-Blocking Layer in High-Power Current Aperture Vertical Electron Transistors (CAVETs)
- Iii-N Transistor With Stepped Cap Layers
- III-N Based Material Structures and Circuit Modules Based on Strain Management

University of California, Santa Barbara
Office of Technology & Industry Alliances
342 Lagoon Road, ,Santa Barbara,CA 93106-2055 |
www.tia.ucsb.edu
Tel: 805-893-2073 | Fax: 805.893.5236 | padilla@tia.ucsb.edu